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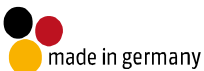
Product Data Sheet
for Nokia

Industrial USB Flash Drive Module

U-58 Series
USB 3.1 SuperSpeed, pSLC

Industrial Temperature Grade

Date: September 13, 2019
Revision: 1.02



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U-58 Series – Industrial USB Flash Drive Module (eUSB)

16 GBytes

1. Product Summary

- **Capacities:** 16 GBytes
- **Form Factor:**
 - USB3.1 solid state flash drive for internal 9(10)-pin USB connector terminal (26.65mm x 36.8mm)
 - 2.54mm or 2.00mm connector with keyed pin
- **Compliance:** USB 3.1 Gen 1 SuperSpeed specification compatible (backward compliance with USB 2.0/1.1)
- **Performance:**
 - Read Performance: Sequential Read up to 180 MBytes/s, Random Read IOPS up to 4,100
 - Write Performance: Sequential Write up to 76 MBytes/s, Random Write IOPS up to 1,680
- **Operating Temperature Range ¹:**
 - Industrial: -40 °C to 85 °C
- **Storage Temperature Range:** -40 °C to 85 °C
- **Operating Voltage:** 3.3V ±5% or 5V ± 10%
- **Data Retention:** 10 Years @ Life Begin; 1 Year @ Life End
- **Endurance in TeraBytes Written (TBW) @ 16 GBytes²:**
 - Enterprise Workload ≥ 67.2
- **Shock/Vibration:** 1,500 *g* / 50 *g*
- **High-Performance 32-Bit Processor with Integrated, Parallel Flash Interface Engines:**
 - Triple-Level Cell (TLC) 3D NAND Flash in pSLC mode
 - Hardware BCH Code ECC (up to 60bit correction per 1 KByte page)
- **High Reliability:**
 - Mean Time Between Failure (MTBF): > 3,000,000 hours
 - Data Reliability: < 1 non-recoverable error per 10¹⁶ bits read

¹ Adequate airflow is required to ensure the drive temperature, as reported in the S.M.A.R.T. data, does not exceed the specified maximum operating temperature.

² According to JEDEC (JESD471), the time to write the full TBW is a minimum of 18 months. Higher average daily data volume reduces the specified TBW. The values listed are estimates and are subject to change without notice.

2. Product Features

- Page based Flash management for increased endurance & random performance
- Optimized FW algorithms especially for high read access and long data retention applications
 - Proven power fail management for highest reliability
 - Near Miss ECC technology
Minimize the risk of uncorrectable bit failure over the product life time. Each read command analyzes the ECC margin level and refreshes data if necessary.
 - Read Disturb Management
The read commands are monitored and the content is refreshed when critical levels have occurred.
 - Wear Leveling technology
Equal wear leveling of static and dynamic data. The wear leveling assures that dynamic data as well as static data is balanced evenly across the memory. This guarantees the maximum write endurance of the device.
 - Data Care Management
The interruptible background process controls the user data for read disturb effects or high temperature related retention degradation and refreshes data if necessary.
- Detailed S.M.A.R.T. support and extended vendor information
- LED for operation indication
- In-field firmware update
- Swissbit Life Time Monitoring (SBLTM) tool and SDK for SBLTM (on request)
- Controlled BOM & PCN process
- Customized options like registers, removable device, connector options, write protect switch, grounded mounting hole, densities, uploads, label, etc.



3. Ordering Information

Table 1: Standard Product List

Capacity	Temperature	
	Commercial	Industrial
	Part Number	Part Number
16 GBytes	SFUI016GcxAE1T0-C-6B-2yP-N01	SFUI016GcxAE1T0-I-6B-2yP-N01

c = connector, x = product generation, y = firmware revision

Table 2: Available Part Numbers

Industrial Temperature		
Capacity	Part Number	Connector
16 GBytes	SFUI016GJ1AE1T0-I-6B-2AP-N01	2.54mm pitch

4. Product Description

The Swissbit U-58 USB 3.1 embedded USB flash drive provides a robust, high performance, and reliable storage product with industry compatible interface and small form factor. The U-58 pSLC technology both enables high 3D TLC NAND flash operation and excellent endurance. The use of page based Flash management and a global wear leveling extends the endurance to unprecedented values for USB products.

The 10-pin connector makes easy integration into existing or newly designed system boards possible. The U-58 is compatible with standard on-board USB connectors that use a single USB 2.0 or USB 3.1 channel. It may not be used in mainboard USB 2.0 connectors that support two USB channels per socket. The embedded USB module serves applications which utilize USB products as acceleration cache for HDDs or as a boot media, for example networking and telecommunication systems.

For outdoor use or in poorly ventilated systems the U-58 is available in industrial temperature grade from -40°C to +85°C. Each individual industrial temperature grade drive is tested at these corners to verify the temperature resistance.

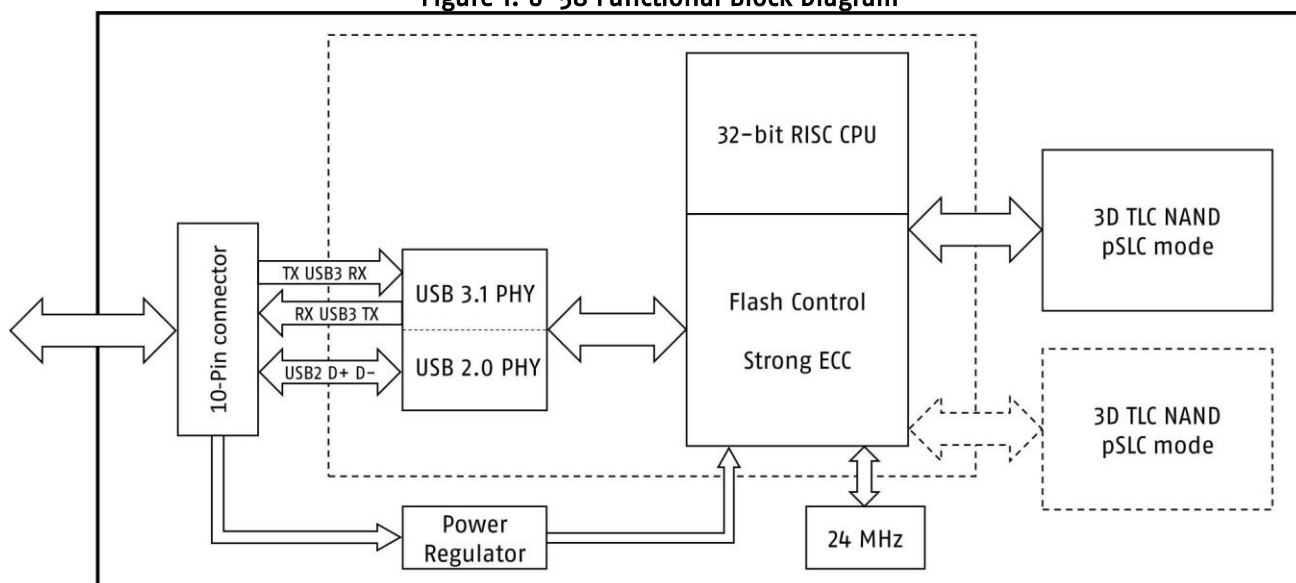
The U-58 firmware includes data care management features which refresh storage areas that are not or only infrequently read. At high temperature storage these areas are prone to retention loss. The firmware monitors the state of the NAND blocks and refreshes those that show a high level of degradation, thus preventing uncorrectable errors. This is an important feature for USB flash drives that are used as read only boot media.

The U-58 consists of a high performance 32bit RISC USB controller, the 10pin connector, power circuitry and different numbers of NAND dies.

The U-58 can flexibly operate at 3.3V or 5V nominal with $\pm 5\%$ tolerance.

It supports USB 3.1 Gen 1 SuperSpeed and is fully backwards compatible to USB 2.0/1.1 High/Full Speed.

Figure 1: U-58 Functional Block Diagram



4.1 Performance Specifications

The U-58 read/write sequential and random CDM performance benchmarks are detailed in the following Table 3 and Table 4.

Table 3: Read/Write Performance in SuperSpeed mode³

Capacity	Sequential Read (MBPS)	Sequential Write (MBPS)	Random Read 4K (IOPS)	Random Write 4K (IOPS)
16 GBytes	180	76	4,100	1,680

Table 4: Read/Write Performance in High-Speed mode³

Capacity	Sequential Read (MBPS)	Sequential Write (MBPS)	Random Read 4K (IOPS)	Random Write 4K (IOPS)
16 GBytes	39	30	2,970	1,500

4.2 Current Consumption

The drive-level current consumption as a function of operating mode is shown in the following Table 5.

Table 5: Current Consumption⁴

Drive Capacity	Sequential Read	Sequential Write	Random Read 4K	Random Write 4K	Idle	Unit
16 GBytes	146	120	92	98	41	mA

³ The values are measured using CrystalDiskMark 5.1.2 x64 (CDM) with Seq Q1T1 and 4KiB Q8T8. Performance depends on flash type and number, file/cluster size, and burst speed.

⁴ All values are the typical recorded at 25 °C, with 5V supply voltage at fastest CrystalDiskMark 5.1.2 x64 (CDM) in SuperSpeed mode.

4.3 Environmental Specifications

4.3.1 Recommended Operating Conditions

The recommended operating conditions for the U-58 USB flash drives are provided in the following Table 6.

Table 6: Recommended Operating Conditions⁵

Parameter	Value
Commercial Operating Temperature	0 °C to 70 °C
Industrial Operating Temperature	-40 °C to 85 °C
Power Supply V _{CC} Voltage	3.3 V ± 5% or 5.0 V ± 10%

4.3.2 Recommended Storage Conditions

The recommended storage conditions are listed in the following Table 7.

Table 7: Recommended Storage Conditions

Parameter	Value
Commercial Storage Temperature	-40 °C to 85 °C ⁶
Industrial Storage Temperature	-40 °C to 85 °C ⁶

4.3.3 Shock, Vibration and Humidity

The maximum shock, vibration and humidity conditions are listed in the following Table 8.

Table 8: Shock, Vibration and Humidity

Parameter	Value
Non-Operating Shock	1,500 g (JESD22-B110, IEC 60068-2-27)
Non-Operating Vibration	50 g (IEC 60068-2-6, MIL-STD-883 M2007.3)
Humidity (Non-Condensing)	85% RH 85 °C, 1000 hrs (JESD22-A101)

⁵ Adequate airflow is required to ensure the drive temperature, as reported in the S.M.A.R.T. data, does not exceed the specified maximum operating temperature.

⁶ The retention at high temperature is reduced. The acceleration factor at 85°C compared with 40°C is 170, i.e. the initial endurance at 10 years@40°C is reduced to 22 days@85°C.

4.4 Regulatory Compliance

The U-58 devices comply with the standards listed in the following Table 9.

Table 9: Regulatory Compliance

Compliance	Country	Type	Standard(s)/Directive
CE	European Union	Compliance	2014/30/EU EN 55032:2015 EN 61000-6-4:2007 +A1:2011 EN 55035:2017 EN 61000-6-2:2005/AC:2015 EN 61000-4-2:2009
FCC	United States	Compliance	47 CFR Part 15, class B
RoHS	European Union	Compliance	2011/65/EU, 2015/863
WEEE	European Union	Compliance	2012/19/EU
REACH	European Union	Compliance	1907/2006
UL	United States	Compliance	Conformity by subparts

4.5 Mechanical Specifications

Physical dimensions are detailed in the following Table 10. Figure 2 on page 13 illustrates the U-58 dimensions.

Table 10: Measured Physical Dimensions

Physical Dimensions		Unit
Length	36.8±0.15	mm
Width	26.65±0.15	
Thickness (Max)	9.7±0.25	
Weight (Max Capacity)	5	g

4.6 Reliability and Endurance

The Mean Time Between Failure (MTBF) is specified to exceed the value listed in the following Table 11. Data reliability with effective error tolerance and data retention at the beginning and end of life is also provided.

Table 11: Reliability

Parameter	Value
MTBF (at 25 °C)	> 3,000,000 hours
Data Reliability	< 1 Non-Recoverable Error per 10 ¹⁶ Bits Read
Data Retention	10 Years at Start (JESD47), 1 Year at EOL

Endurance represented as both TeraBytes Written (TBW) and full Drive Writes Per Day (DWPD) is provided in the following Table 12.

Table 12: Endurance⁷

Drive Capacity	Enterprise	
	TBW	DWPD ⁸
16 GBytes	67.2	3.8

4.7 Drive Geometry Specification

Table 13: Drive Geometry

Raw Capacity	Total LBA	User Addressable Bytes
	Decimal	(Unformatted)
16 GBytes	31,326,208	16,039,018,496

⁷ Enterprise workload follows the JEDEC JESD219 standard. Enterprise workload values are measured based on 168 hours of runtime.

1 TByte = 10¹² bytes

⁸ DWPD values are based on a service life of 3 years

5. Electrical Interface

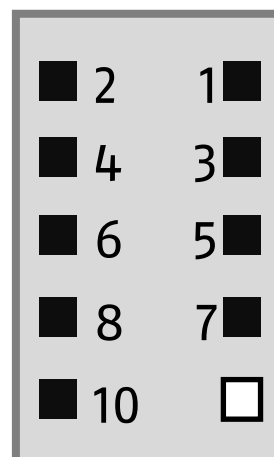
- USB connector 10pin (2mm or 2.54mm pitch)
- **Do not connect the drives to a standard USB2 host pin header with two USB 2.0 ports!**
If pin 2 has 5V at the host side, it can destroy the USB3 SSRX+ input of the device.
- USB 3.1 Gen1 SuperSpeed interface, USB2.0 high-speed and 1.1 full-speed compatible

Table 14: Electrical pinout from device and host view.

Never connect >1.8V to pin2 and pin4.

Pin	Signal device view	Signal host view	Description host view
1	V_Bus	V_Bus	Operating voltage
2	SSRX+	SSTX+	Host transmit +
3	D-	D-	Data signal pair
4	SSRX-	SSTX-	Host transmit -
5	D+	D+	Data signal pair
6	GND	GND	Ground
7	GND	GND	Ground
8	SSTX+	SSRX+	Host receive +
9	-	-	Keyed at connector
10	SSTX-	SSRX-	Host receive -

See also chapter 7 Package Mechanical



6. Electrical Specification

Table 15: Absolute Maximum Ratings

Parameter	Symbol	Min	Max	Unit
Power Supply Voltage	V_Bus	-0.5	6.0	V
Voltage at D+ and D-	V_Data	-0.5	5.0	
Voltage at USB3 pins	V_Data	-0.5	1.8	
Commercial Operating Temperature	T_A	0	70	°C
Industrial Operating Temperature		-40	85	

Table 16: DC characteristics for SuperSpeed operation (T=25°C, V_Bus=5V)

Parameter	Symbol	Density	Min	Typ	Max	Unit
Supply Voltage	V_Bus	all	3.1	3.3 or 5.0	5.50	V
Write current	I_WR	16 GBytes		120	132	mA
Read current	I_RD	16 GBytes		146	161	
Idle current	I_IDL	all		41 ⁹	45	
Suspend current	I_CCS	all		1.9	2.5	

Table 17: DC characteristics for High-Speed operation (T=25°C, V_Bus=5V)

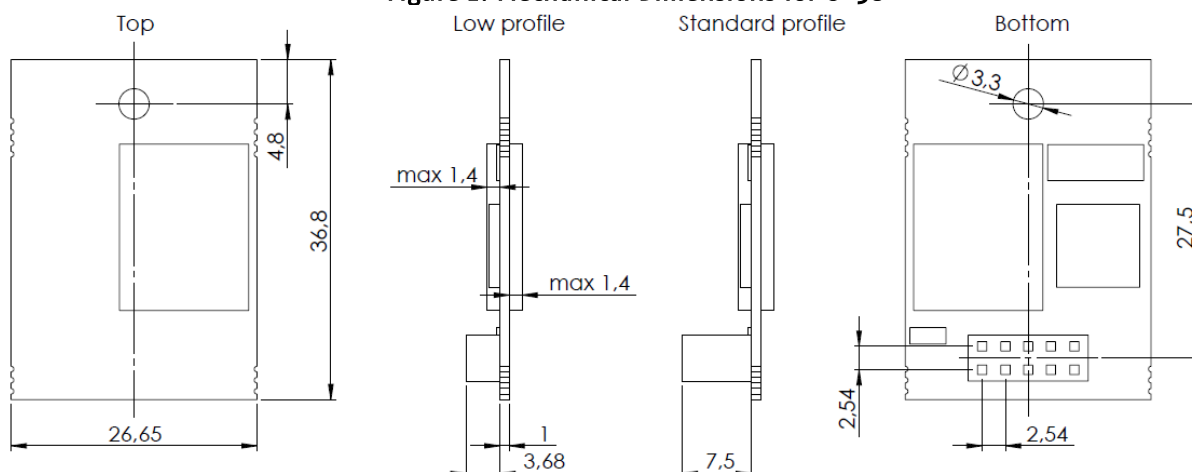
Parameter	Symbol	Density	Min	Typ	Max	Unit
Supply Voltage	V_Bus	all	3.1	3.3 or 5.0	5.50	V
Write current	I_WR	16 GBytes		61	67	mA
Read current	I_RD	16 GBytes		67	74	
Idle current	I_IDL	all		36 ⁹	40	
Suspend current	I_CCS	all		2.1	2.5	
High Speed Idle Level	V_HSOI	all	-10		10	mV
High Speed Data Signaling LOW	V_HSOL	all	-10		10	
High Speed Data Signaling HIGH	V_HSOH	all	360		440	
Chirp J Level (differential)	V_CHIRPJ	all	360		440	
Chirp K Level (differential)	V_CHIRPK	all	-440		-360	

⁹ Typically 5 minutes after power on the device performs a background data care management, that needs up to 119mA in SuperSpeed and 112mA in High-Speed mode.

7. Package Mechanical

- Standard form factor of PCBs 36.8mm x 26.65mm
- Hole for mechanical fixture (optional grounded)
- 3 additional holes
- LED for operation indication (optional without LED)
- 2 connector types
 - 2.54mm pitch, 7.5mm long standard
 - 2.00mm pitch, 3.68mm long low profile
- Component heights max. 1.4mm on connector side
max. 1.4mm on flash side

Figure 2: Mechanical Dimensions for U-58



All dimensions are in millimeters, tolerance: ± 0.15

8. ATA Pass-Through commands (Identify Device and S.M.A.R.T.)

8.1 ATA Pass-Through commands

Additional to the standard SCSI commands the device also supports the ATA Pass-Through commands.

Table 18: ATA PASS-THROUGH(x) commands

SCSI command	OpCode	Description
ATA PASS-THROUGH(12)	A1h	Write and read ATA registers to send commands and read information
ATA PASS-THROUGH(16)	85h	

<http://www.t10.org/ftp/t10/document.04/04-262r8.pdf>

Table 19: ATA register addressing

Offset address	Input	Output	Type	Identify device	e.g. SMART commands
0	Data		Word		
1	Feature	Error	Byte	xx	yyh*
2	Sector count		Byte	xx	01h
3	LBA_Low		Byte	xx	xx
4	LBA_Mid		Byte	xx	4Fh
5	LBA_High		Byte	xx	C2h
6	Drive/head		Byte	E0h	E0h
7	Command	Status	Byte	ECh	B0h

* see below

8.2 Identify Device

The Identify Device returns a identify sector compatible to ATA and SATA devices.
Here an example of the interpretation of this sector.

Table 20: Identify Device Information

Word(s)	Default Value		Total Bytes	Data Field Type Information
0	0040h		2	Standard Configuration Fixed (optional 848Ah for removable)
...	...	...	...	...
10-19	aaaa*		20	Serial number in ASCII (right-justified)
...	...	...	...	...
23-26	XXXX*		8	Firmware revision in ASCII (big-endian byte order in Word)
27-46	XXXX*		40	Model number in ASCII (right-justified)
...	...	...	...	...
60-61	XXXXh		4	Total number of sectors addressable in LBA mode
...	...	...	...	...
82	0101h 7701h* 4063h*		2	Command set: SMART feature set, service interrupt
...	...	...	...	...
85	000Xh 0701h* 4063h*		2	Command set enabled: SMART feature set enabled/disabled
...	...	...	...	...
255	XXA5h		2	Integrity Word

* Values depend on device configuration.

8.3 S.M.A.R.T. commands

The intent of the SMART command feature set is to protect user data and minimize the likelihood of unscheduled system downtime that may be caused by predictable degradation and/or fault of the device. By monitoring and storing critical performance and calibration parameters, SMART feature set devices attempt to predict the likelihood of a near-term degradation or fault condition. Providing the host system the knowledge of a negative reliability condition allows the host system to warn the user of the impending risk of a data loss and advise the user of the appropriate action.

All S.M.A.R.T. commands have the command code Boh. The different commands are selected by the Feature register.

Table 21: S.M.A.R.T. Features Supported

Operation	Feature	Sect Count	LBA low	LBA mid	LBA high	DRV head	Com- mand
S.M.A.R.T. Read Data	D0h	01h	xx	4Fh	C2h	E0h	Boh
S.M.A.R.T. Read Attribute Thresholds	D1h	01h	xx	4Fh	C2h	E0h	Boh
S.M.A.R.T. Enable Operations	D8h	xx	xx	4Fh	C2h	E0h	Boh
S.M.A.R.T. Disable Operations	D9h	xx	xx	4Fh	C2h	E0h	Boh
S.M.A.R.T. Return Status	DAh	xx	xx	4Fh	C2h	E0h	Boh

All commands are aborted, if the LBA signature is invalid.

8.3.1 S.M.A.R.T. Read Data (Doh)

When the drive receives the S.M.A.R.T. Read Data subcommand, it returns one sector (512 bytes) of data. See the following table for the data structure of this sector.

Table 22: S.M.A.R.T. Data Structure

Byte(s)	Value	Description
0-1	0010h	S.M.A.R.T. structure version
2-361	XXh	Attribute entries 1 to 30 (see Table 23)
362	00h	Off-line data collection status (no off-line data collection started)
363	00h	Self-test execution status byte (self-test completed)
364-365	0000h	Total time, in seconds, to complete off-line data collection
366	00h	Vendor specific
367	00h	Off-line data collection capability (no off-line data collection)
368-369	0003h	S.M.A.R.T. capabilities
370	00h	No Error logging capability
371	00h	Vendor specific
372	00h	Short self-test routine recommended polling time, in minutes
373	00h	Extended self-test routine recommended polling time, in minutes
374-385	00h	Reserved
386-387	0004h	SMART Version
388-510	XXh	Vendor specific
511	XXh	Data structure checksum

8.3.2 S.M.A.R.T. Attribute Entry Structure

Each attribute entry (Bytes 2–361) consists of 12 bytes. See the following table for the data structure of each entry.

Table 23: Attribute Entry

Offset Byte(s)	Value	Description
0	XXh	Attribute ID (see Table 24)
1–2	XXXXh	Flags (little-endian) Bit0: Advisory (0) or Prefailure (1) Bit1: Not used (0) or updated during normal operation (1)
3	XXh	Current value as a percentage 64h = 100%
4	XXh	Worst value as a percentage 64h = 100%
5–10	XXXXh	Raw value (little-endian)
11	00h	Reserved

8.3.3 S.M.A.R.T. Attributes

The drives support the S.M.A.R.T. attributes listed in the following table.

The Threshold values can be read out with the S.M.A.R.T. Read Attribute Thresholds command (D1h)

The first attributes (196, 213, 229) are “Pre-Fail” type, while all other are Advisory (Old Age).

Table 24: S.M.A.R.T. Attributes

ID dec	ID hex	Value	Worst	Thres-hold	Attribute	Description	RAW values Offset 5–10
196	C4h	X%	X%	25	Spare Block Count	Number of total available NAND spare blocks	Initial (offset 5–7) and current (offset 8–10) number of spare blocks
213	D5h	X%	X%	25	Spare Block Count worst channel	Spare block count for the NAND with the lowest number of remaining spare blocks	Initial (offset 5–7) and current (offset 8–10) number of spare blocks of the channel with the lowest current number of spare blocks
229	E5h	X%	X%	2	Total Erase Count	Estimated number of total NAND block erases	Estimated number of total NAND block erases
203	CBh	100	100	0	Total ECC Errors	All recorded ECC errors	Total number of ECC errors (correctable and uncorrectable) (offset 5–8)
204	CCh	100	100	0	Correctable ECC Errors	Total recorded ECC errors that were corrected during the life of the drive	Total number of correctable ECC errors (offset 5–8)
199	C7h	100	100	0	UDMA CRC Errors	Dummy attribute, included for legacy reasons	This value is fixed at 0.
232	E8h	100	100	0	Total Number of Reads	Total number of NAND READ commands	Total number of NAND READ commands
12	0Ch	100	100	0	Power-On Count	Count of power-on events	Number of power cycles (offset 5–8)
241	F1h	100	100	0	Total LBAs Written	Total amount of data written to the drive	Total number of LBAs written to the disk, divided by 65536
242	F2h	100	100	0	Total LBAs Read	Total amount of data read from the drive	Total number of LBAs read from the disk, divided by 65536
214	D6h	100	100	0	Management Block status	Total number of times the management block has been updated	Management block write count (offset 5–8)
215	D7h	X%	X%	0	Trim Status	Amount of device content that is currently in the trimmed state	This value is fixed at 0.

ID dec	ID hex	Value	Worst	Thres-hold	Attribute	Description	RAW values Offset 5-10
194	C2h	X°C	Max °C	0	Temperature Status	Device temperature in Celsius (°C)	Current (offset 5) / Min (offset 6) / Max temperature (offset 7)

* These threshold values are changeable using the Write Attribute Thresholds command.

8.3.4 S.M.A.R.T. Read Attribute Thresholds (D1h)

When the drive receives the S.M.A.R.T. Read Attribute Thresholds subcommand, it returns one sector (512 bytes) of data similar as S.M.A.R.T. Read data sector, but with the threshold value in offset 1 of each attribute (see Table 24).

8.3.5 S.M.A.R.T. Enable Operations (D8h)

This command enables access to the S.M.A.R.T. capabilities of the drive. The state of SMART (enabled or disabled) is preserved across power cycles.

8.3.6 S.M.A.R.T. Disable Operations (D9h)

This command disables access to the S.M.A.R.T. capabilities of the drive. The state of SMART (enabled or disabled) is preserved across power cycles.

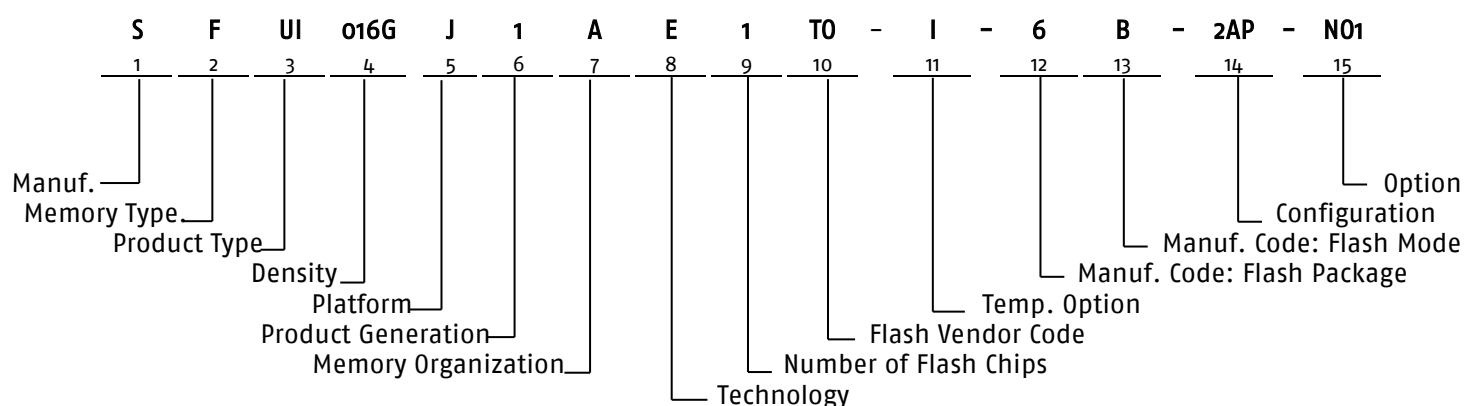
8.3.7 S.M.A.R.T. Return Status (DAh)

Table 25: S.M.A.R.T. Return Status

Operation	Feature	Sect Count	LBA low	LBA mid	LBA high	DRV head	Com-mand
Command S.M.A.R.T. Return Status	DAh	xx	xx	4Fh	C2h	Eoh	Boh
Response							
S.M.A.R.T. Return Status OK	xx	xx	xx	4Fh	C2h	xx	xx
S.M.A.R.T. Return Status Pre-FAIL*	xx	xx	xx	F4h	2Ch	xx	xx

* If a threshold exceeded condition exists for either the Spare Block Count Worst Channel attribute or the Erase Count attribute, the device will set the Cylinder Low register to F4h and the Cylinder High register to 2Ch. In this case the drive should be replaced soon.

9. Part Number Decoder



9.1 Manufacturer

Swissbit code	S
---------------	---

9.2 Memory Type

Flash	F
-------	---

9.3 Product Type

U-xxx USB Flash Drive Module (Internal)	UI
---	----

9.4 Density

8 GBytes	008G
16 GBytes	016G
32 GBytes	032G
64 GBytes	064G

9.5 Platform

U-xxx – 2.54mm plug	J
U-xxx – 2.00mm plug	K

9.6 Product Generation

First generation	1
------------------	---

9.7 Memory Organization

x8	A
----	---

9.8 Technology

U-5xx platform UFD	E
--------------------	---

9.9 Number of Flash Chips

1 Flash	1
2 Flash	2

9.10 Flash Code

Toshiba	T0
---------	----

9.11 Temperature Option

Commercial Temperature Range: 0 °C to 70 °C	C
Industrial Temperature Range: -40 °C to 85 °C	I

9.12 Die Classification

3D TLC MONO (single die package)	5
3D TLC DDP (dual die package)	6
3D TLC QDP (quad die package)	7
3D TLC ODP (octal die package)	8

9.13 Pin Mode

	BGA	TSOP
Single nCE and Single R/nB	A	S
Dual nCE and Dual R/nB	B	T
Quad nCE and Quad R/nB	C	U
Octal nCE and Octal R/nB	V	*

*Not Available

9.14 Configuration XYZ

X = Configuration

Configuration	X
Removable Drive	1
Fixed Drive	2

Y = Firmware Revision

FW Revision	Y
Revision 1	A

Z = Optional setting

Optional Setting	Z
Default (SLC or MLC)	1
pSLC (pseudo SLC)	P

9.15 Option

Swissbit / Standard	STD
Customized version	N01

10. Marking Specification

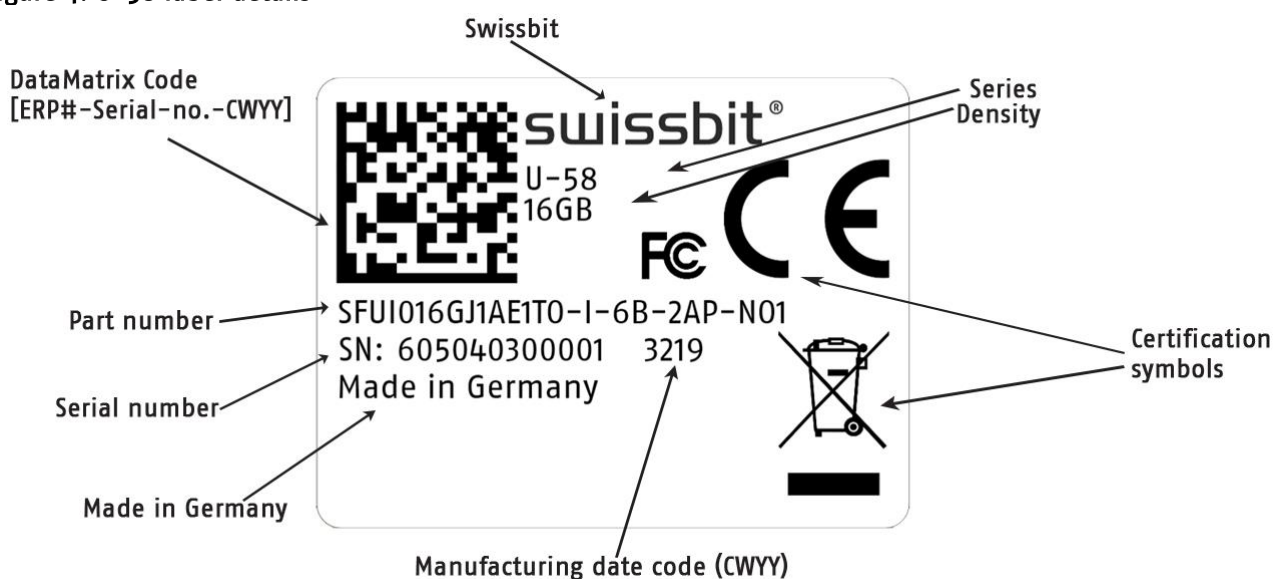
10.1 Top View

Figure 3: U-58 top view



10.2 Label content

Figure 4: U-58 label details



11.Revision History

Table 26: Document Revision History

Date	Revision	Description	Revision Details
24-Jul-2019	1.00	Initial release	Doc. req. no. 3079
09-Aug-2019	1.01	Rebranding the U-56 3D NAND pSLC product variants to 'U-58 Series' for better differentiation	Doc. req. no. 3121
13-Sep-2019	1.02	Adjustment of the Supply Voltage data in Table 16 and Table 17, Correction in Table 12	Doc. req. no. 3175

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